

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
600V	260mΩ@10V	14A

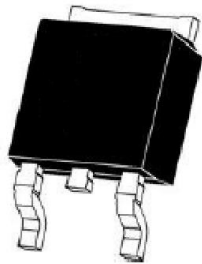
Feature

- Optimized body diode reverse recovery performance
- Low on-resistance and low conduction losses
- Ultra Low Gate Charge cause lower driving requirements
- ESD protected

Application

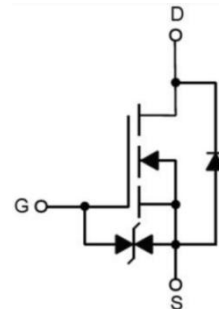
- Power factor correction (PFC)
- Switched mode power supplies(SMPS)
- Uninterruptible Power Supply (UPS)
- LLC Half-bridge

Package

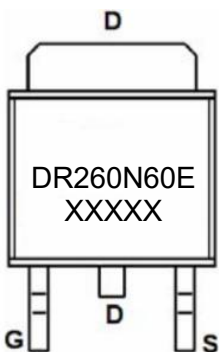


TO-252AB

Circuit diagram



Marking



Absolute maximum ratings (Tc=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	600	V
Gate-Source Voltage,AC (f>1 Hz)	V _{GS}	±30	V
Gate-Source Voltage,DC	V _{GS}	±20	V
Continuous Drain Current	I _D	14	A
Continuous Drain Current(T _C =100°C)	I _D (100°C)	9.8	A
Pulsed Drain Current ¹⁾	I _{DM}	42	A
Power Dissipation	P _D	128	W
Thermal Resistance,Junction-to-Case	R _{θJC}	1.17	°C/W
Single pulse avalanche current ²⁾	I _{AS}	2.5	A
Junction Temperature	T _J	175	°C
Storage Temperature Range	T _{STG}	-55 ~ +175	°C

Electrical characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D =250μA	600			V
Zero gate voltage drain current(T _C =25°C)	I _{DSS}	V _{DS} =600V,V _{GS} = 0V			10	μA
Zero gate voltage drain current(T _C =125°C)	I _{DSS}	V _{DS} =600V,V _{GS} = 0V			300	μA
Gate-body leakage current	I _{GSS}	V _{GS} =±20V, V _{DS} = 0V			±200	nA
Gate threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	3.5	4.2	5.0	V
Drain-source on-resistance	R _{DS(on)}	V _{GS} =10V, I _D =7A		230	260	mΩ
Dynamic characteristics³⁾						
Input Capacitance	C _{iss}	V _{DS} =50V,V _{GS} =0V, f =1MHz		946		pF
Output Capacitance	C _{oss}			50		
Reverse Transfer Capacitance	C _{rss}			1.6		
Total Gate Charge	Q _g	V _{DS} =400V,V _{GS} =10V, I _D =7A		19		nC
Gate-Source Charge	Q _{gs}			9.8		
Gate-Drain Charge	Q _{gd}			3.1		
Gate Plateau Voltage	V _{gp}			6.8		
Gate Resistance	R _g	f =1MHz,D-S short		17.3		Ω
Turn-on delay time	t _{d(on)}	V _{DD} =380V,V _{GS} =10V, I _D =7A,R _G =4Ω		18		nS
Turn-on rise time	t _r			13		
Turn-off delay time	t _{d(off)}			52		
Turn-off fall time	t _f			10		
Source-Drain Diode characteristics						
Diode Forward voltage	V _{SD}	V _{GS} =0V, I _{SD} =14A, T _J =25°C			1.2	V
Diode Forward Current	I _{SD}	T _C =25°C			14	A
Pulsed-Source-drain current	I _{SDM}				42	A
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = 7A di/dt = 100A/μs		85		nS
Reverse Recovery Charge	Q _{rr}			0.29		uC
Peak reverse recovery current	I _{rrm}			7		A

Notes:

- 1) Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2) T_J=25°C, V_{DD}=50V, V_G=10V, R_G=25Ω.
- 3) Guaranteed by design, not subject to production.

Typical Characteristics

Figure1. Safe operating area

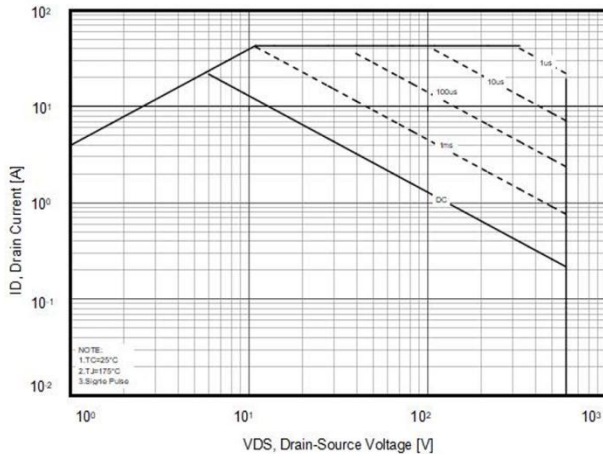


Figure2. Source-Drain Diode Forward Voltage

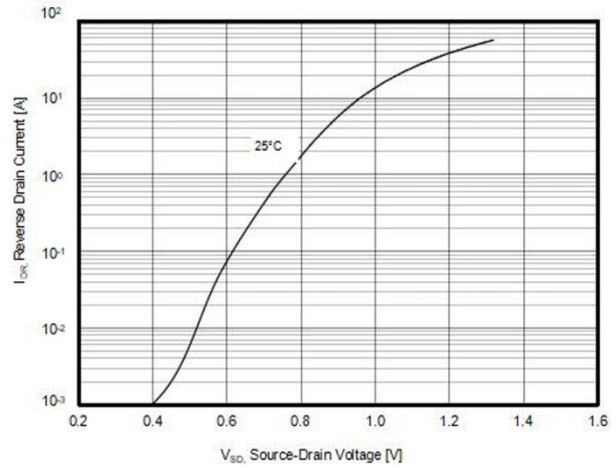


Figure3. Transfer characteristics

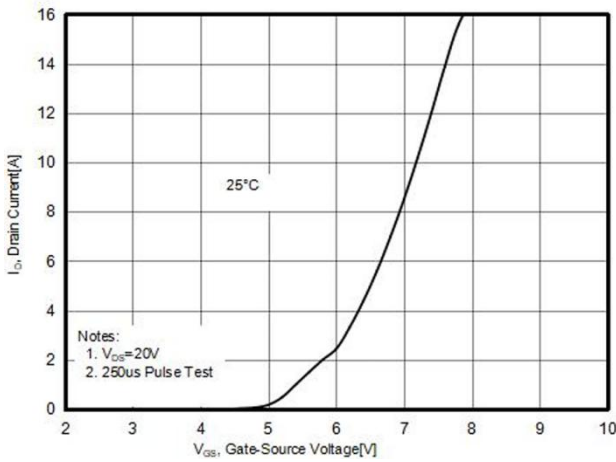


Figure4. Output characteristics

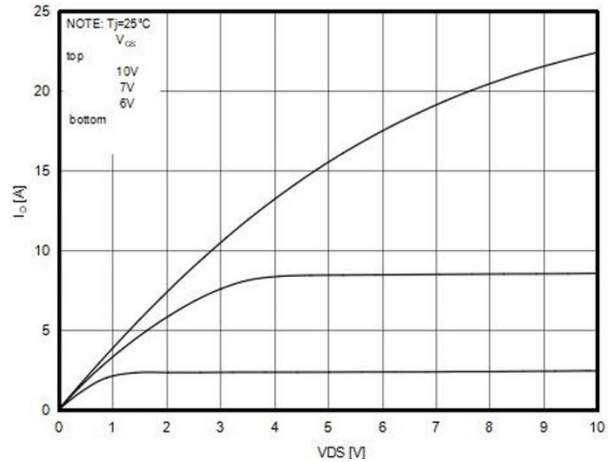


Figure5. Static drain-source on resistance

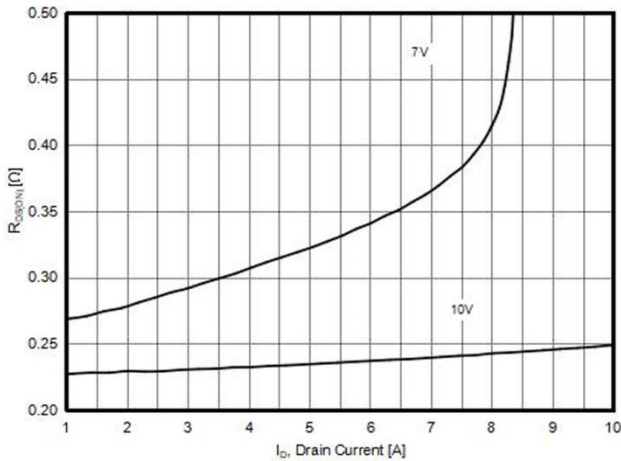
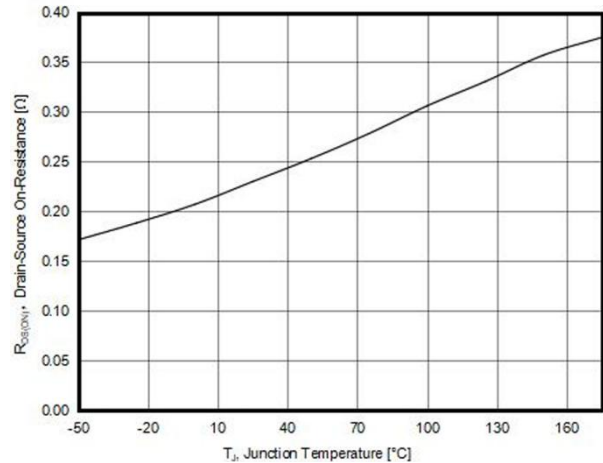


Figure6. $R_{DS(ON)}$ vs Junction Temperature



Typical Characteristics

Figure7. BV_{DSS} vs Junction Temperature

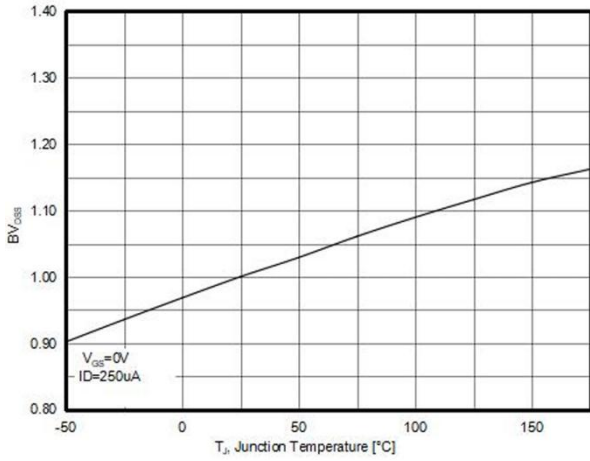


Figure8. Maximum I_D vs Junction Temperature

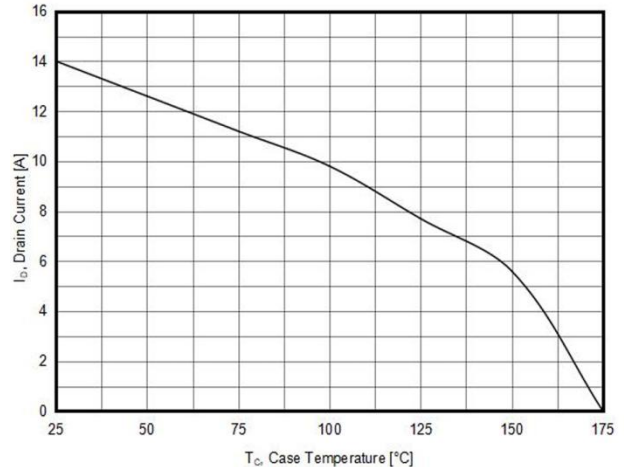


Figure9. Gate charge waveforms

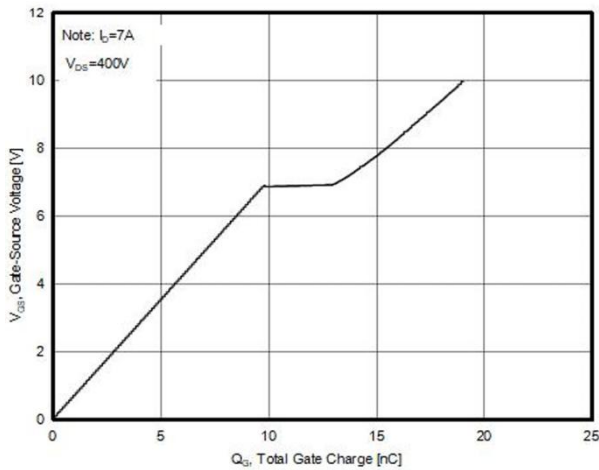
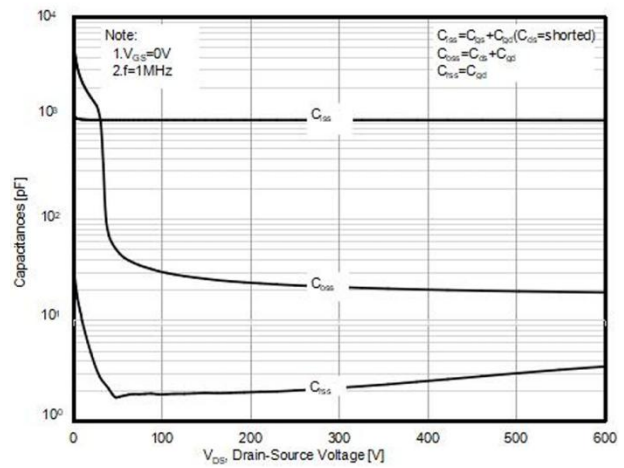
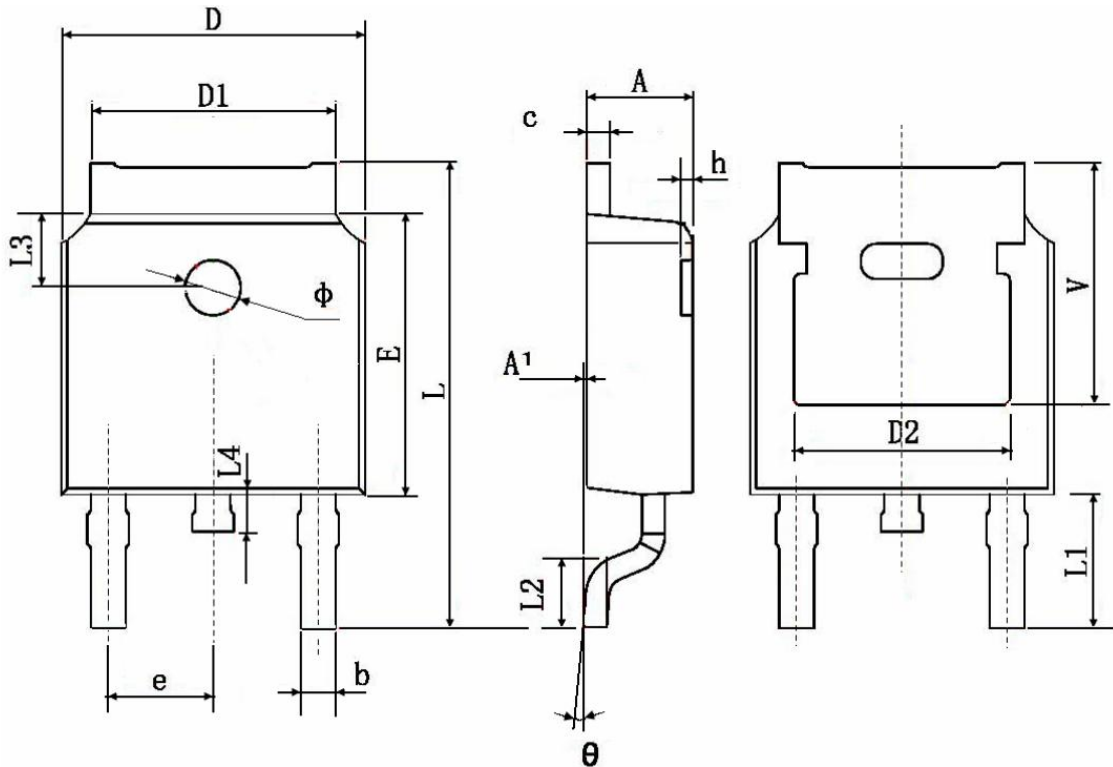


Figure10. Capacitance



TO-252AB Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.130	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.500	0.201	0.217
D2	4.830 REF.		0.190 REF.	
E	6.000	6.200	0.236	0.244
e	2.186	2.390	0.086	0.094
L	9.800	10.500	0.386	0.413
L1	2.900 REF.		0.114 REF.	
L2	1.400	1.800	0.055	0.070
L3	1.600 REF.		0.063 REF.	
L4	0.600	1.000	0.024	0.039
phi	1.100	1.300	0.043	0.051
theta	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012